

In the Specification:

As requested in the amendment filed January 6, 2005, please substitute the following Title of the application for the Title as originally filed at all occurrences in the application:

ELECTROSTATIC DISCHARGE SEMICONDUCTOR PROTECTION
CIRCUIT OF REDUCED AREA

Additionally, please substitute the following paragraph for the corresponding paragraph beginning at Page 7, line 2 in the specification as originally filed.

Preferably, the semiconductor device further comprising comprises a second diffused region (45) connected to the diffused region (44) so that the PN junction (D1) is formed with the defused diffused region (44).

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binder amendment
MSF
8/8/05